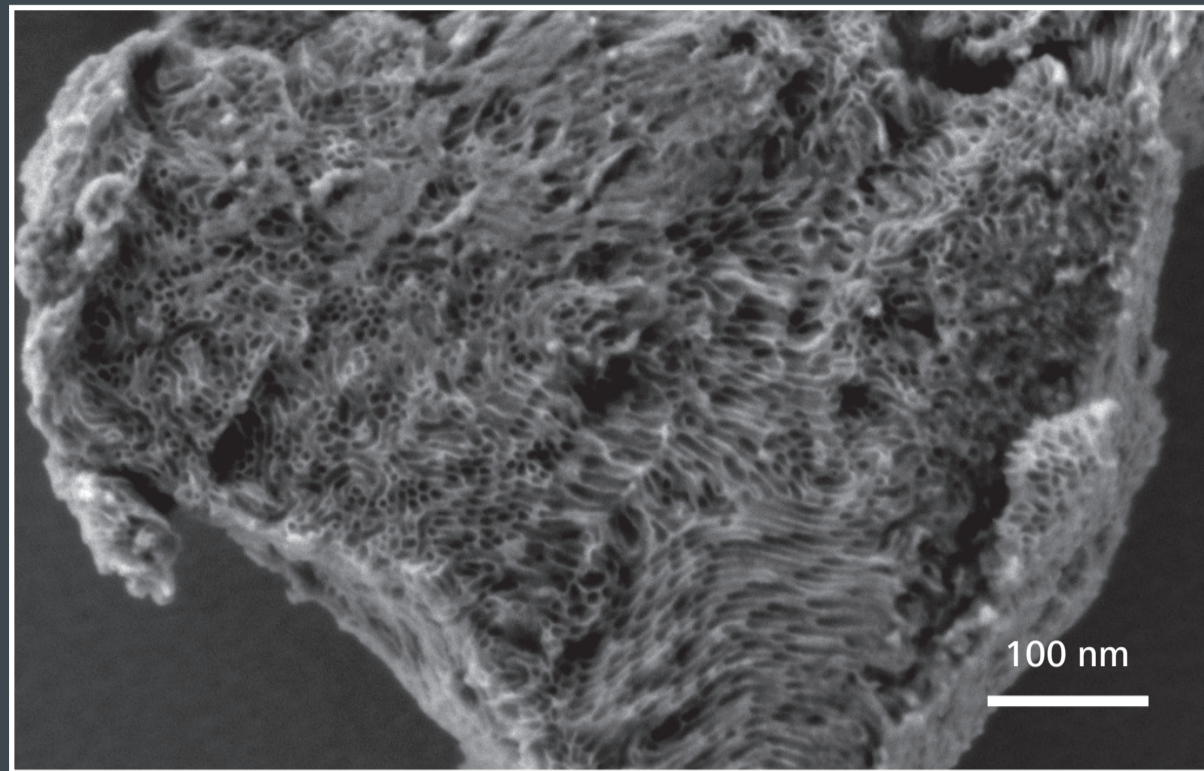
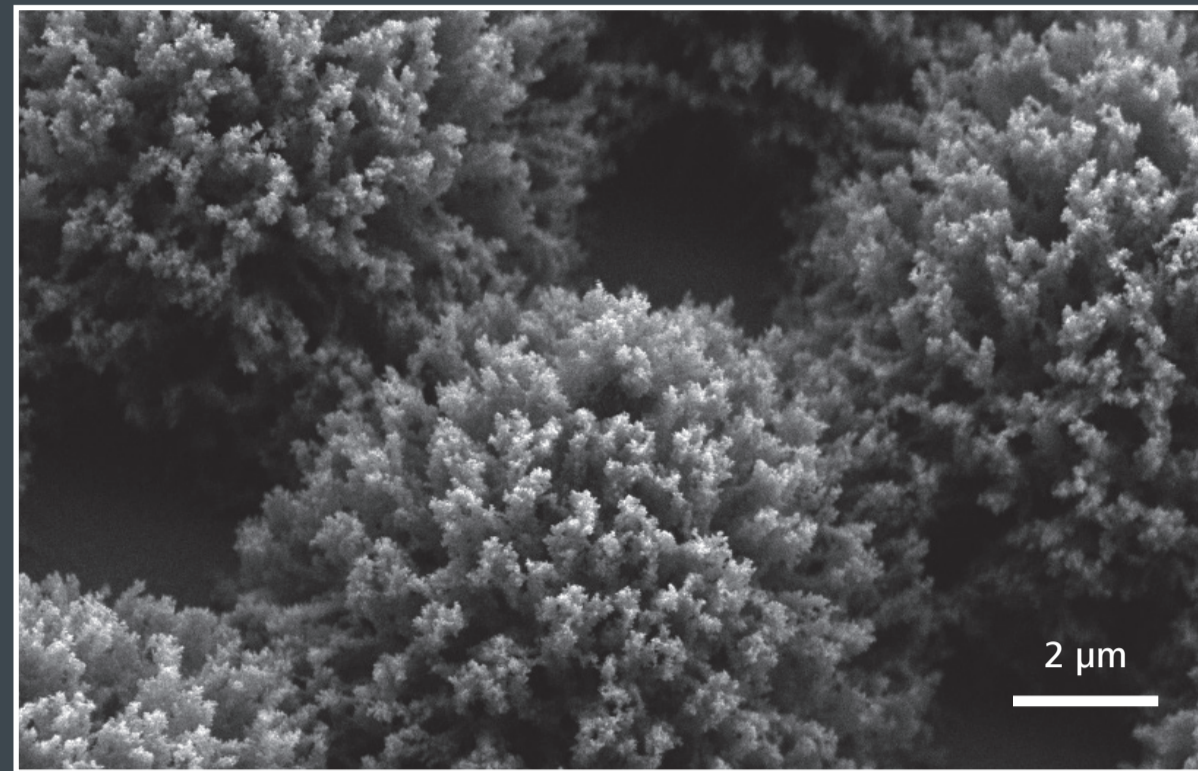


ZEISS Gemini Optics

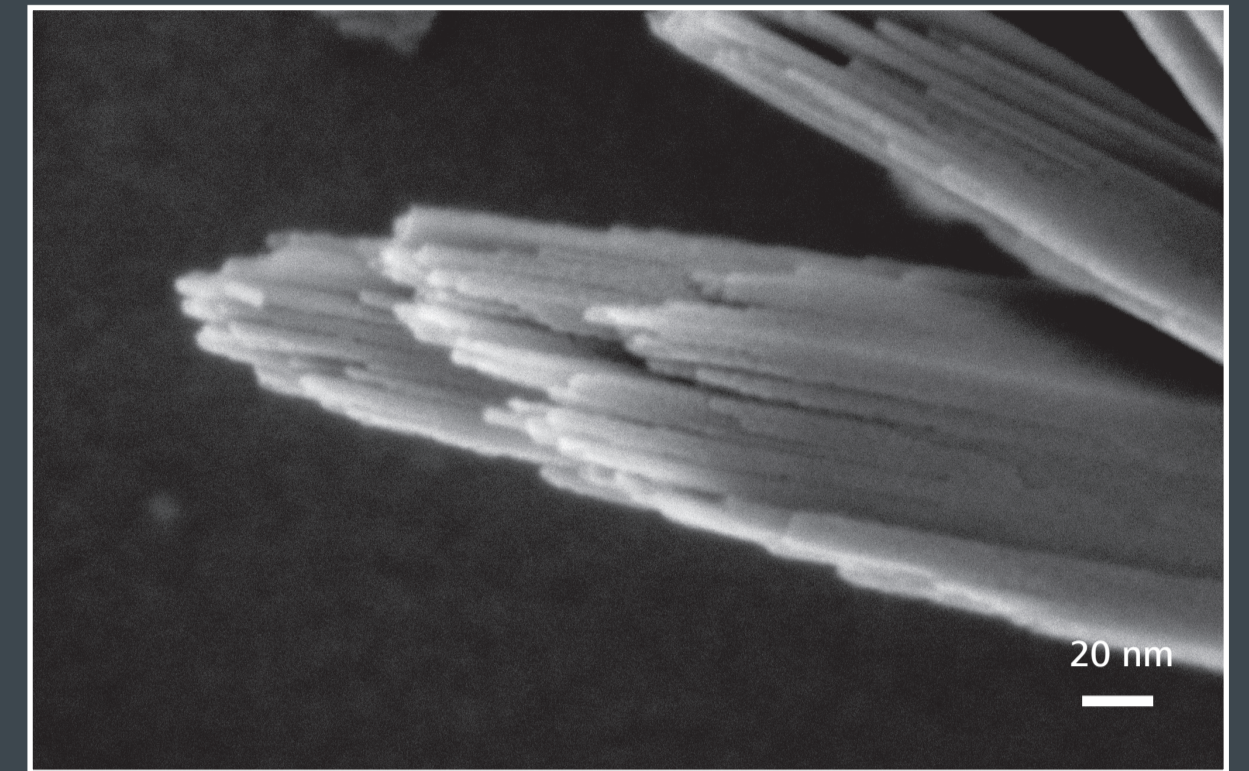
High Resolution Images On Real World Samples



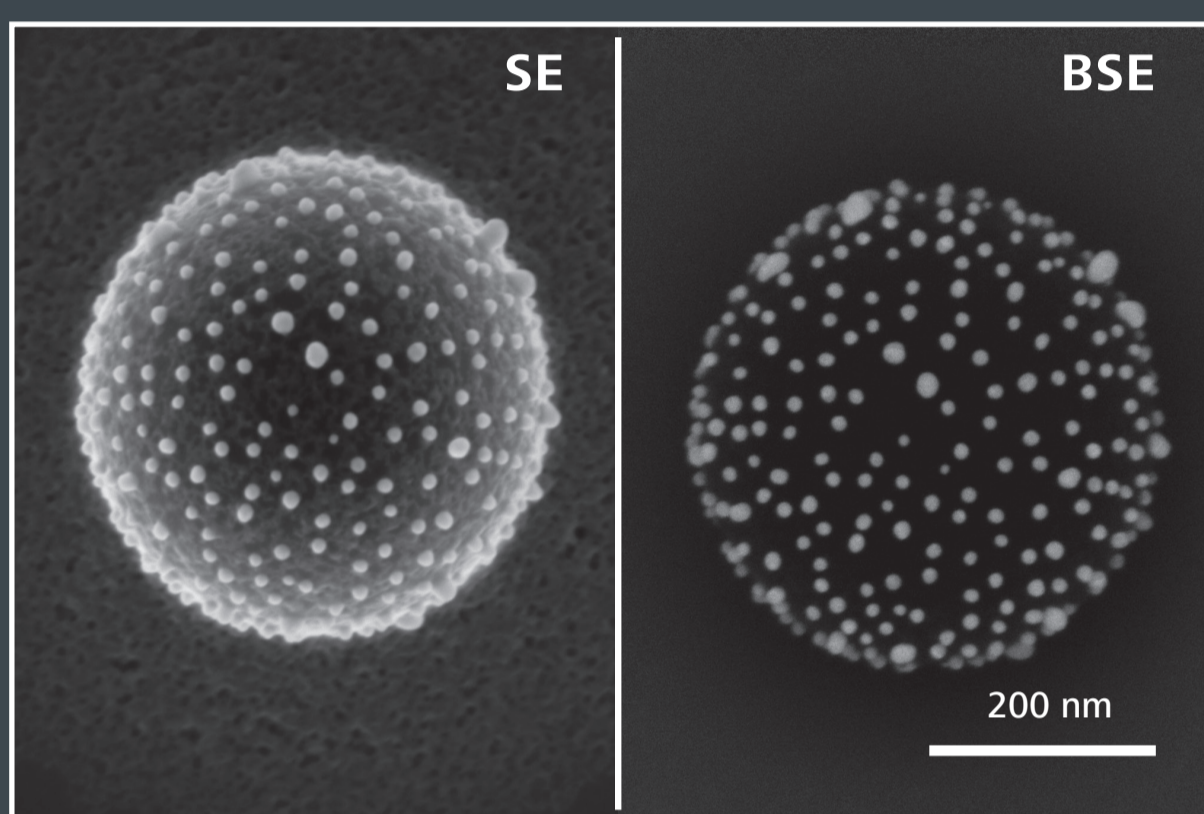
Mesoporous silica. Imaged with Inlens SE detector at 500V.



Platinum nanostructures sputtered on nickel dendrites. Imaged with Inlens SE at 1.5kV.



Nanometer spaced FeO(OH) crystals. Imaged with Inlens SE detector at 1kV.

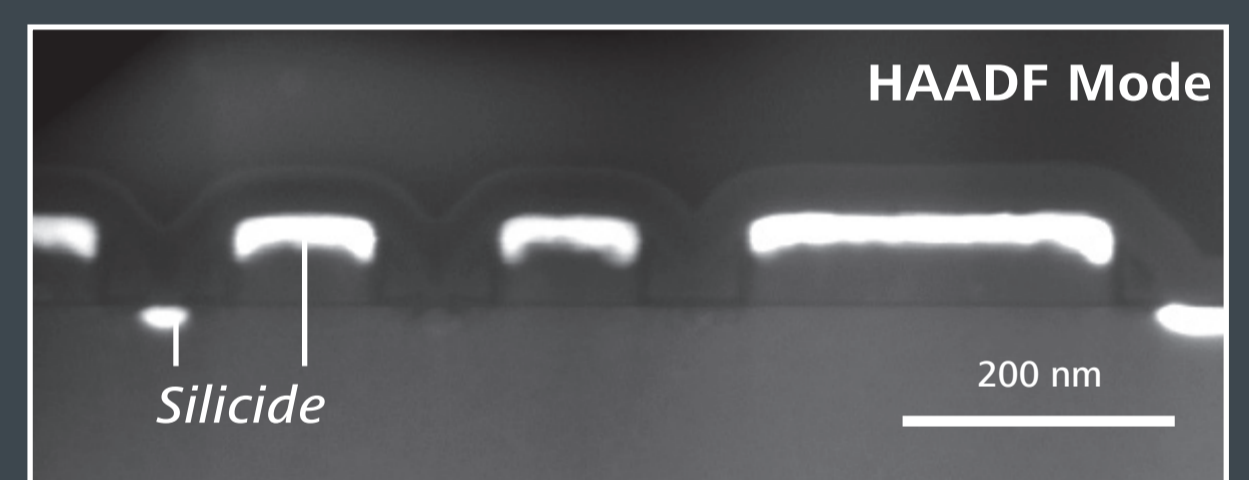
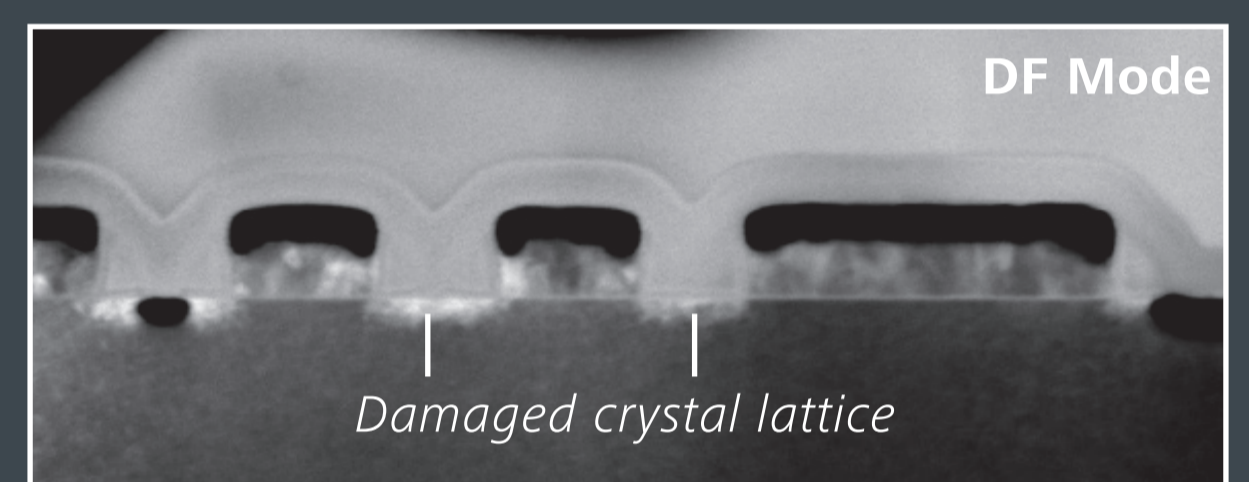
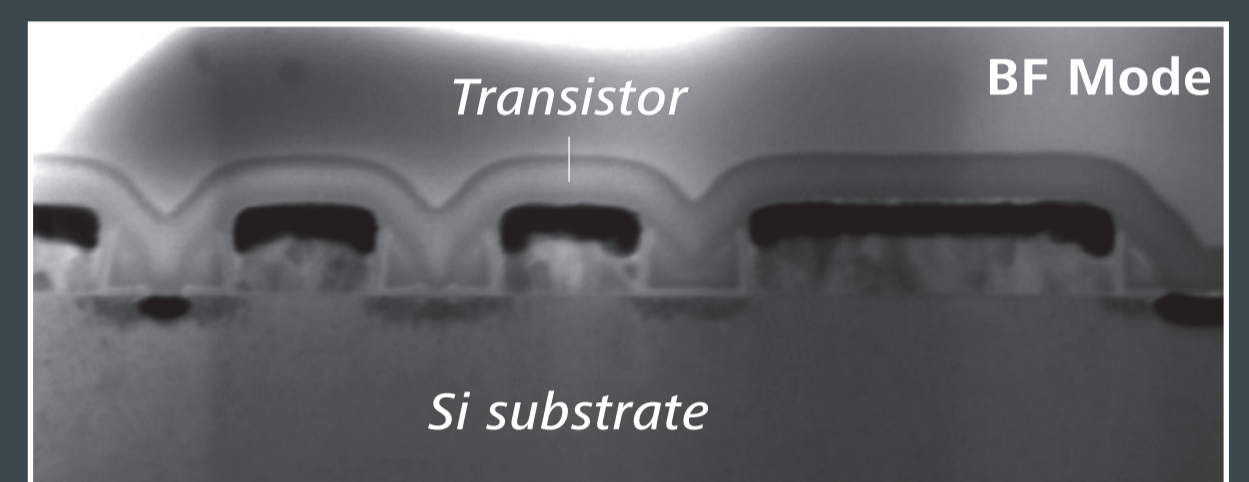
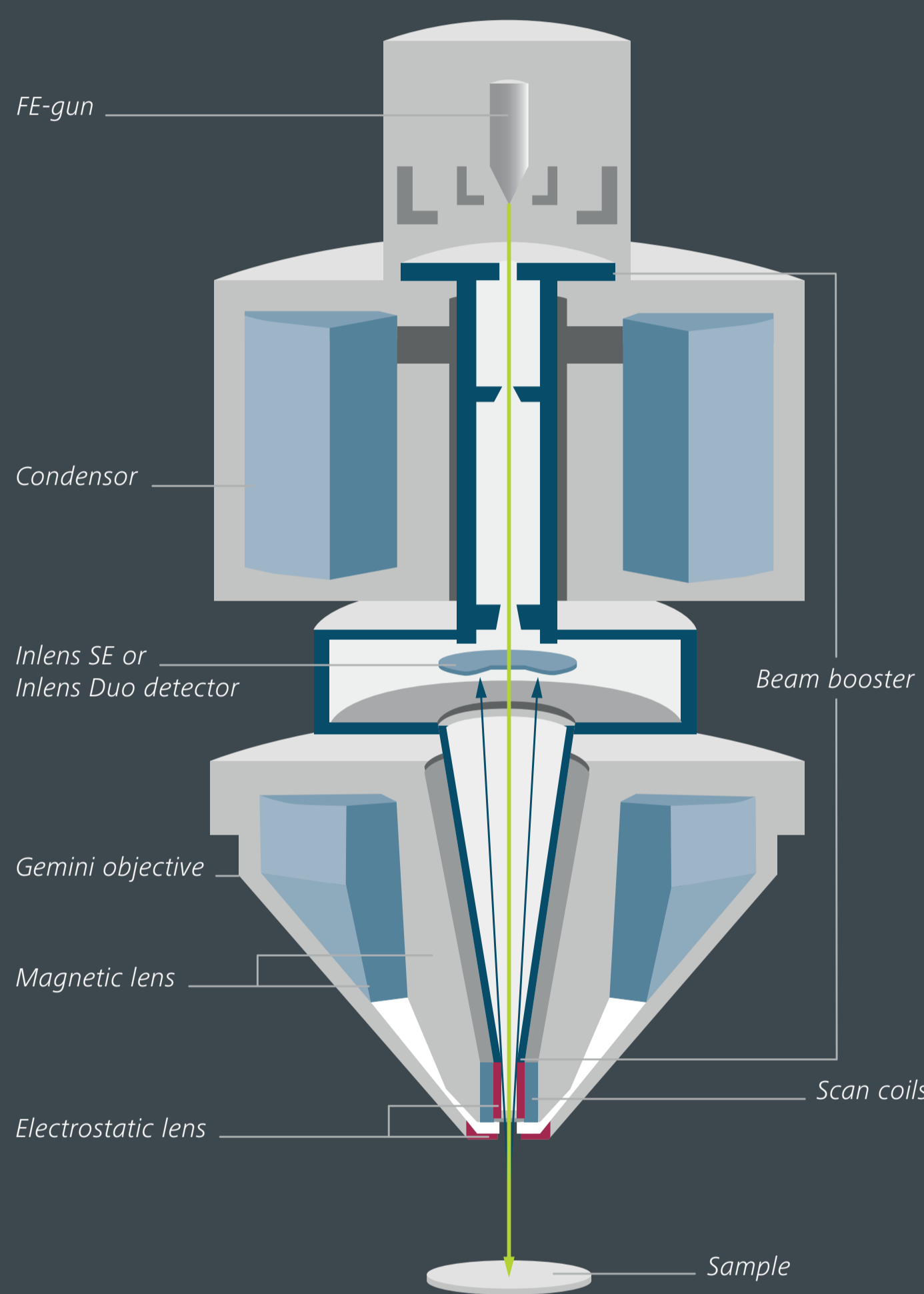


Gold nanoparticles on polystyrene sphere. Imaged simultaneously at 3kV.

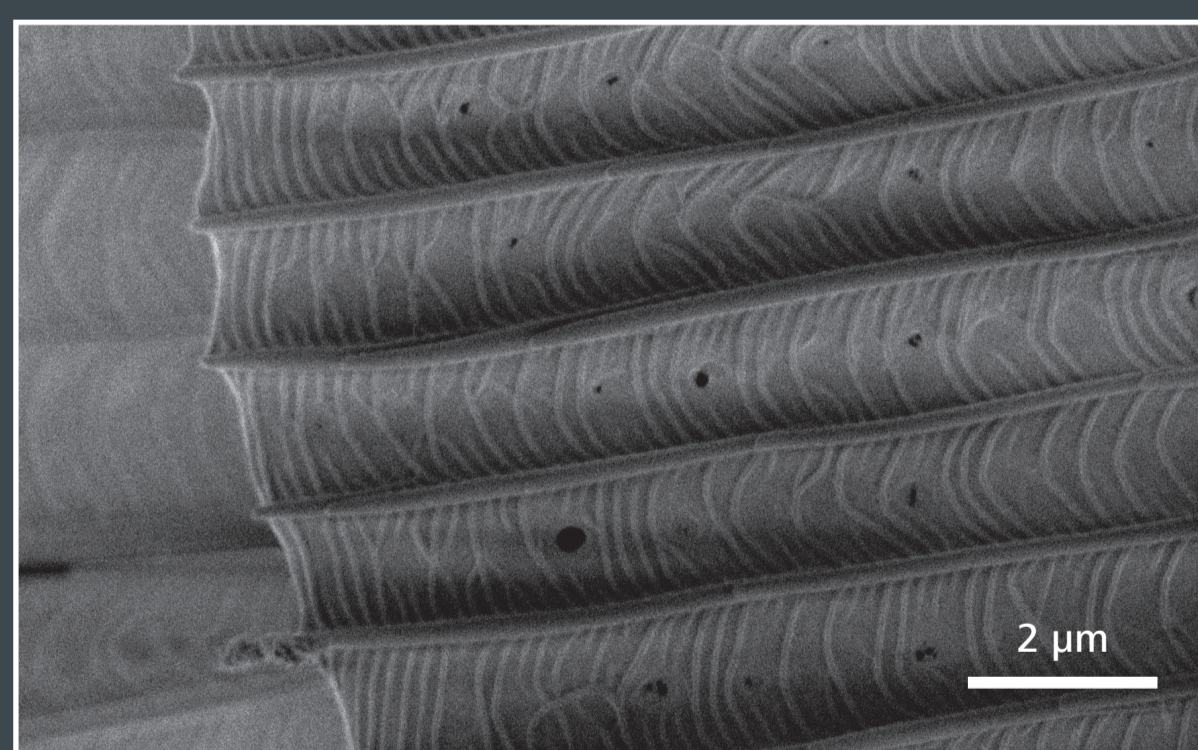
Left: Inlens SE image, surface topography. Right: EsB image, material contrast.



FinFET transistor. Top view, 22 nm technology, pure BSE imaging using EsB, at 3kV with high material contrast.



45 nm semiconductor device imaged with annular-STEM. The diffraction contrast in brightfield (BF) and darkfield (DF) images reveal damaged crystal lattice at ion implanted Si regions. High-angle annular darkfield (HAADF) captures mass scattering effect to give highest contrast of the silicide.



Moth wing. Inlens SE detector, at 50V, in high vacuum. No charging effect if ultra-low voltage like 50V is applied.

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Seeing beyond